EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	366	getter near4 (surface or lid or cover) and cavity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:22
L2	119	getter near4 (surface or lid or cover) same cavity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:23
L3	34	getter near4 (surface or lid or cover) same cavity and (cavity near8 cover)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:23
L4	22	getter near4 (surface or lid or cover) same cavity and (cavity near8 cover) and ((device or circuit) near4 (substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:32
L5	3	getter near4 (surface or lid or cover) same cavity and (cavity near8 cover) and ((device or circuit) near4 (substrate or wafer)) and (vacuum near4 chamber)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:24
L6	2	getter near4 (surface or lid or cover) same cavity and (cavity near8 cover) and ((device or circuit) near4 (substrate or wafer)) and (vacuum near4 chamber) and (degree same vacuum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:25
L7	35939	degree near4 vacuum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:33

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L8	10484	degree near4 vacuum and (vacuum near4 chamber)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:33
L9	162	degree near4 vacuum and (vacuum near4 chamber) and (adjust near4 degree)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:33
L10	2	degree near4 vacuum and (vacuum near4 chamber) and (adjust near4 degree) and (getter near4 cavity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:34
L11	2	degree near4 vacuum and (vacuum near4 chamber) and (adjust near4 degree) and getter	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:38
L12	3973	((device or circuit) near4 (substrate or wafer or semiconductor)) same (vacuum near chamber)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:42
L13	39	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 "inert gas")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:44
L14	0	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 "inert gas") and (control near4 atmosphere)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:44

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L15	1	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 "inert gas") and (control near4 pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:45
L16	67	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and (control near4 pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:46
L17	0	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and (control near4 pressure) and ((cover or lid) near8 (device or circuit))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:47
L18	2	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and (control near4 pressure) and ((cover or lid) near8 getter)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:48
L19	2	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and (control$4 or detect$4 or measur$4 near4 pressure) and ((cover or lid) near8 getter)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:49
L20	2	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and ((control$4 or detect$4 or measur$4) near4 pressure) and ((cover or lid) near8 getter)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:49
L21	2	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and ((control$4 or detect$4 or measur$4 or calculat$4) near4 pressure) and ((cover or lid) near8 getter)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 12:50

L22	2	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and ((control$4 or detect$4 or measur$4 or calculat$4 or adjust$4) near8 pressure) and ((cover or lid) near8 getter)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 13:10
L23	0	((device or circuit) near4 (substrate or wafer or semiconductor)) same ((vacuum near chamber) near4 gas) and ((control$4 or detect$4 or measur$4 or calculat$4 or adjust$4) near8 pressure) and ((cover or lid) near8 getter) and (438/48-50.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/14 13:10
S1	9	MEMS and getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 12:28
S2	109	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:47
S3	1	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4 and titanium and time and argon and discharg$4 and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48
S4	25	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4 and titanium and time and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48
S5	144	adhes$4 and conduct$4 and binder and filler and (heat$4 or thermal or temperature) and pressuriz$4 and viscosity and connect and (hard$4 or solid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:08

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S6	16	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10
S7	10	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond and argon and time and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10
S8	3	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:11
S9	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
S10	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
S11	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:13
S12	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:17
S13	7	MEMS and titanium and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:24

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S14	16970	getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:25
S15	216	(getter near titanium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:26
S16	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
S17	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber) and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
S18	3	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
S19	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
S20	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S21	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32

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S22	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S23	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S24	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S25	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and (bond or attach)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:33
S26	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:12
S27	0	(getter near titanium) and (cover near glass) and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
S28	0	getter near glass and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
S29	220	"anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13

S30	9	"anodic bond" and getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
S31	6	"anodic bond" and getter and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
S32	6	"anodic bond" and getter and glass and cover	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
S33	6	"anodic bond" and getter and glass and cover and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:15
S34	2	(("5701008") or ("6499354B1")).PN. or ((2002/0089835A1) or (2003/0085438A1)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/02/16 10:51
S35	0	S34 and getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/02/16 10:59
S36	90	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:00
S37	17	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon and (vacuum near chamber) and glass and (heat or thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:11
S38	1	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon and (vacuum near chamber) and bond and align	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:12

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S39	44	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and (argon or gas or inert) and (vacuum near chamber) and bond and align	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:29
S40	14	(getter near4 cavity) and (vacuum near chamber) and cover and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33
S41	9	(getter near4 cavity) and (vacuum near chamber) and cover and degree and titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33
S42	3	(getter near4 cavity) and (vacuum near chamber) and cover and degree and titanium and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33
S43	7	(getter near8 (cavity or hole or via or trench)) and (cover or lid) and (align$4 near8 (circuit or device)) and sensor and degree and bond$4 and seal$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 13:59
S44	2	(getter near8 (cavity or hole or via or trench)) and (cover or lid) and (align$4 near8 (circuit or device)) and sensor and degree and bond$4 and seal$4 and titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 13:55
S45	0	(getter near8 (cavity or hole or via or trench)) and (cover or lid) and (align$4 near8 (circuit or device)) and sensor and degree and bond$4 and seal$4 and (438/48, 49.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 14:00